WHAT IS CLAIMED IS:

1. A dry etching method comprising the steps of:

preparing a layer to be etched; and

dry-etching said layer using a mask made of a tantalum or a tantalum nitride under a reaction gas of a carbon monoxide with an additive of a nitrogen containing compound gas.

2. A microfabrication method comprising the steps of:

forming a mask made of a tantalum on a layer to be etched; and

dry-etching said layer using said mask under a reaction gas of a carbon monoxide with an additive of a nitrogen containing compound gas.

3. The method as claimed in claim 2, wherein said step of forming a mask includes forming a resist pattern on said layer to be etched and sputtering a mask layer using a tantalum target.

4. A microfabrication method comprising the steps of:

forming a mask made of a tantalum nitride on a layer to be etched; and

dry-etching said layer using said mask under a reaction gas of a carbon monoxide with an additive of a nitrogen

containing compound gas.

5. The method as claimed in claim 4, wherein said step of forming a mask includes forming a resist pattern on said layer to be etched and reactive-sputtering a mask layer using a tantalum target under a reaction gas containing at least a nitrogen gas.

6. The method as claimed in claim 5, wherein said reaction gas containing at least a nitrogen gas is a mixture gas of an argon gas and a nitrogen gas.

7. The method as claimed in claim 4, wherein said step of forming a mask includes forming a resist pattern on said layer to be etched and sputtering a mask layer using a tantalum nitride target.

8. A dry etching mask used in dry-etching under a reaction gas of a carbon monoxide with an additive of a nitrogen containing compound gas, said mask being made of a tantalum or a tantalum nitride.